SE1A THRU SE1M

SURFACE MOUNT HIGH EFFICIENT RECTIFIER

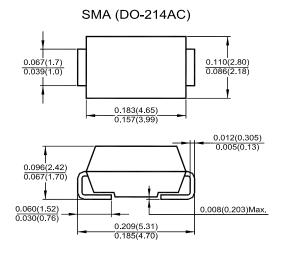
Reverse Voltage - 50 to 1000 V Forward Current - 1 A

Features

- High current capability
- High surge current capability
- High reliability
- Low reverse current
- Low forward voltage drop
- Fast switching for high efficiency

Mechanical Data

- Case: SMA (DO-214AC) molded plastic
- Epoxy: UL 94V-0 rate flame retardant
- Lead: Lead formed for surface mount
- Polarity: color band denotes cathode end
- Mounting position: Any



Dimensions in inches and (millimeters)

Maximum Ratings and Electrical Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Parameter	Symbols	SE1A	SE1B	SE1D	SE1E	SE1G	SE1J	SE1K	SE1M	Units
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	200	300	400	600	800	1000	V
Maximum RMS Voltage	V _{RMS}	35	70	140	210	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	300	400	600	800	1000	V
Maximum Average Forward Current $T_a = 55 \text{ °C}$	I _{F(AV)}	1								А
Maximum Peak Forward Surge Current, 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC method)	I _{FSM}	30								A
Maximum Forward Voltage at $I_F = 1 A$	V _F	1.1					1	.7	2.2	V
Maximum DC Reverse Current $T_a = 25 ^{\circ}C$ at Rated DC Blocking Voltage $T_a = 100 ^{\circ}C$	I _R	5 50							μΑ	
Maximum Reverse Recovery Time ¹⁾	t _{rr}	50 75						ns		
Typical Junction Capacitance ²⁾	CJ	50							pF	
Junction and Storage Temperature Range	T _J , T _{Stg}	- 65 to + 150								°C

¹⁾ Reverse recovery test conditions: $I_F = 0.5 \text{ A}$, $I_R = 1 \text{ A}$, $I_{rr} = 0.25 \text{ A}$

 $^{\rm 2)}$ Measured at 1 MHz and applied reverse voltage of 4 V



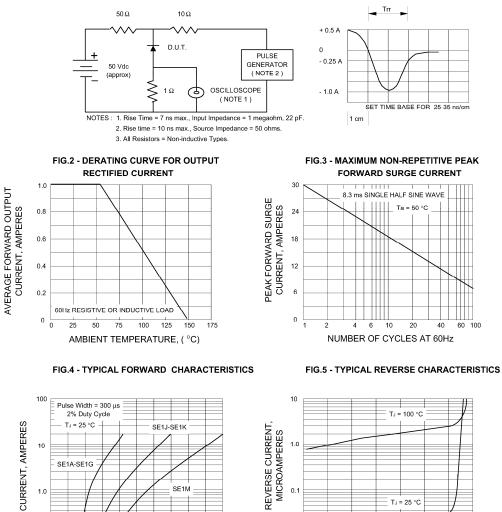
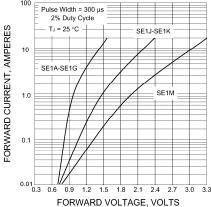


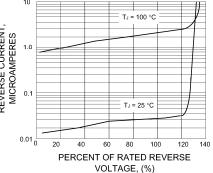
FIG.1 - REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM



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